

/ Descriptions

WR0553I M M E QSQ æ M ç s ll 1 Silicon NPN transistor in a TO-220F Plastic Package.

/ Features

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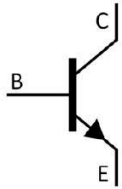
High voltage high speed switching.

/ Applications

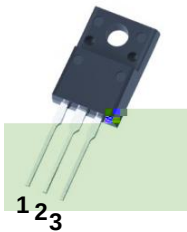
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Switching regulator applications, High voltage switching applications, High speed DC-DC converter applications.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base

PIN 2 χ Collector

PIN 3 χ Emitter

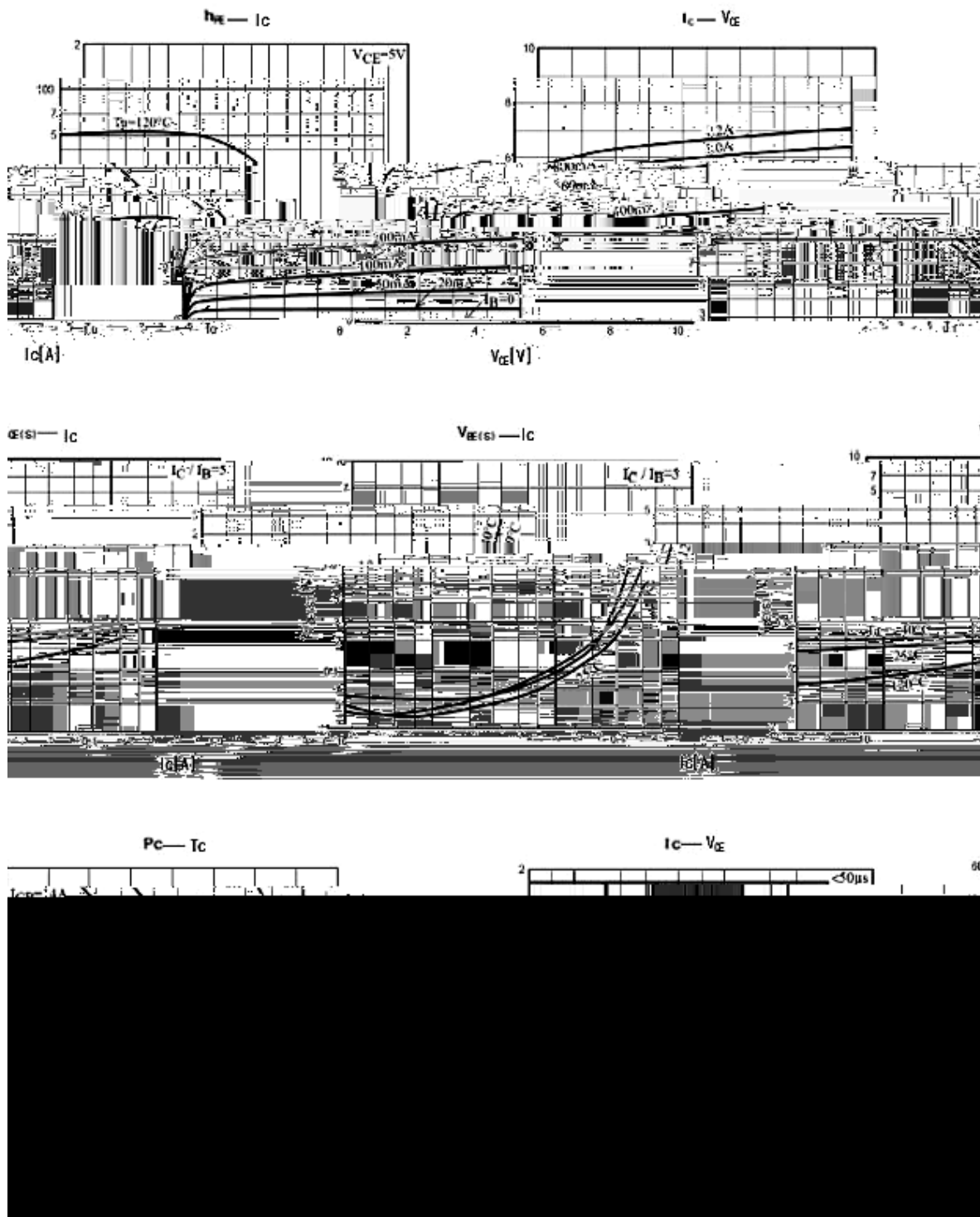
/ h_{FE} Classifications & Marking

ð M ç þ " See Marking Instructions .

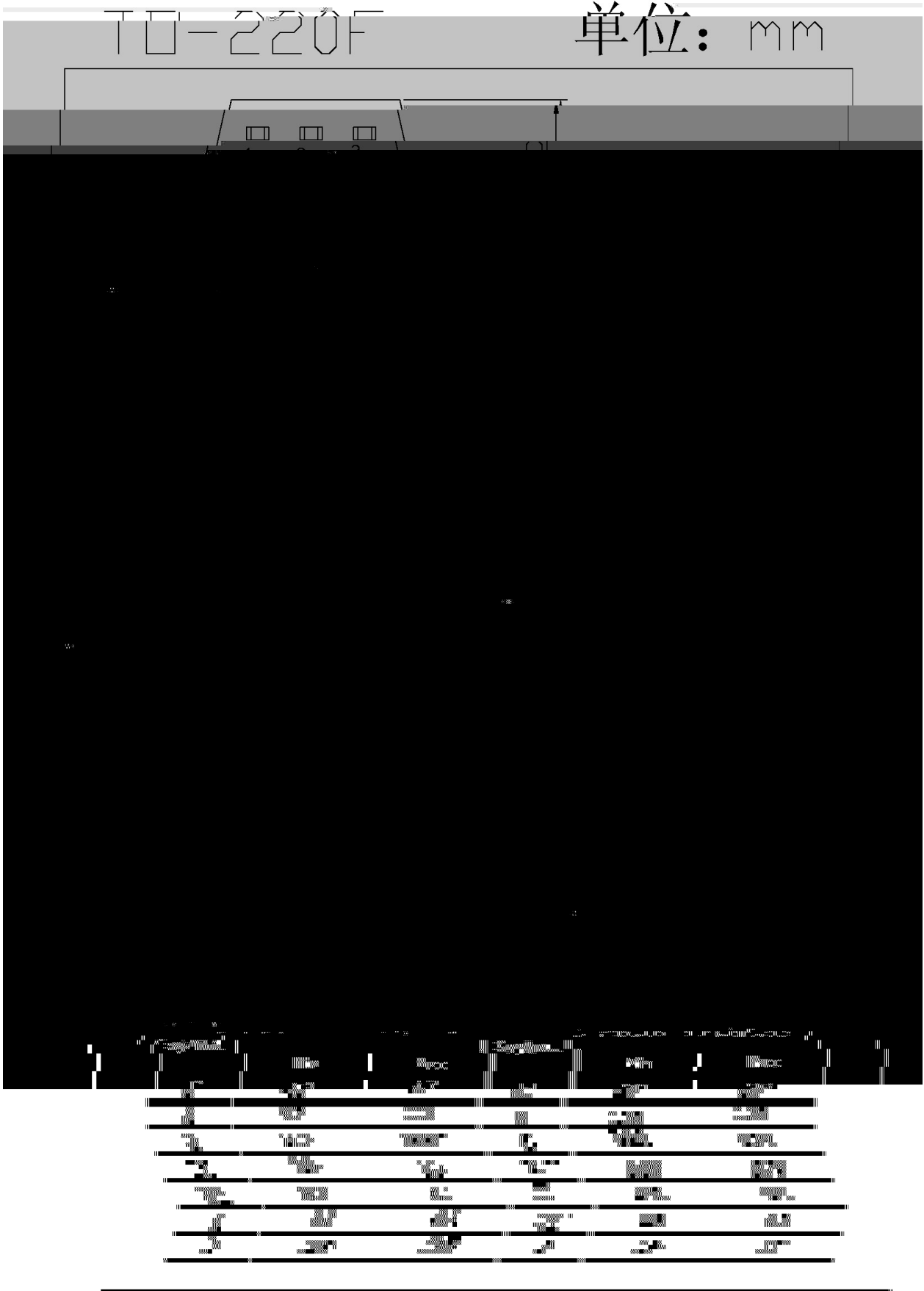
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	900	V
Collector to Emitter Voltage	V_{CEO}	500	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	7.0	A
Peak Collector Current	I_{cm}	14	A
Collector Power Dissipation	$P_C(T_c=25^\circ C)$	45	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=1mA, I_B=0$	900			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA, I_B=0$	500			V
Collector Cut-Off Current	I_{CEO}	$V_{CE}=500V, I_E=0$			250	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5V, I_C=0$			10	μA

/ Electrical Characteristic Curve



/ Package Dimensions



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